

L Number	Hits	Search Text	DB	Time stamp
2	1226	372/6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 13:50
3	9895	lowest near3 order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 13:50
4	1276	lowest near3 order near3 mode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 13:51
5	647	(lowest near3 order near3 mode) and fiber	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 13:51
6	327	(lowest near3 order near3 mode) and fiber and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 14:08
7	29	Princeton near2 Lightwave	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/14 14:12
-	3368	372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 12:18
-	7889	372/43,46.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:24
-	1682	372/50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:25
-	12180	372/43-50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:30
-	1186	372/75.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:29
-	307	372/38.02.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:26
-	135	372/38.01.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:26
-	44	372/38.01,38.02,75.ccls. and (semiconductor and feedback and (longitudinal near3 mode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:46
-	34	372/38.01,38.02,75.ccls. and (semiconductor and feedback and (longitudinal near3 mode) and (resonator or resonating or reflector))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 09:47
-	25068	GaAs near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 10:49
-	3559	(GaAs near3 substrate) and (resonator or resonating or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 10:50

-	180	(GaAs near3 substrate) and (indium and nitrogen) and (resonator or resonating or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 10:51
-	3161	(GaAs near3 substrate) and (indium or In and nitrogen or N) and (resonator or resonating or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 10:52
-	3180	((GaAs or (gallium near3 arsenic)) near3 substrate) and (indium or In and nitrogen or N) and (resonator or resonating or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 10:54
-	272	((GaAs or (gallium near3 arsenic)) near3 substrate) and (indium and nitrogen or (In near1 N)) and (resonator or resonating or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/19 11:11
-	40	nill near3 kenneth or (walpole near3 james)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 12:19
-	146	spatial near3 mode near3 filter	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:24
-	97725	(tilt or tilted or incline or angle) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:25
-	13307	(tilt or tilted) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:27
-	93783	(incline or angle) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:25
-	2041	(tilt or tilted) and angle and semiconductor and fiber	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:28
-	711	(tilt or tilted) and angle and semiconductor and fiber and grating	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:42
-	3391	372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:51
-	751	372/45.ccls. and (tilted or inclined or incline or angled or angle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:51
-	2474	372/43-50,75,38.01,38.02,.ccls. and (tilted or inclined or incline or angled or angle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:52
-	2252	372/43-50,75,38.01,38.02,.ccls. and ((tilted or inclined or incline or angled or angle) and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/24 13:54